

# Phase Control Thyristors (Hockey PUK Version), 990 A



**B-PUK (TO-200AC)** 

PRIMARY CHARACTERISTICS					
I <sub>T(AV)</sub>	990 A				
V <sub>DRM</sub> /V <sub>RRM</sub>	800 V, 1200 V, 1400 V, 1600 V, 1800 V, 2000 V				
$V_{TM}$	1.62 V				
I <sub>GT</sub>	100 mA				
$T_J$	-40 °C to +125 °C				
Package	B-PUK (TO-200AC)				
Circuit configuration	Single SCR				

#### **FEATURES**

- · Center amplifying gate
- Metal case with ceramic insulator
- International standard case B-PUK (TO-200AC)



- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>

#### **TYPICAL APPLICATIONS**

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
1		990	A			
I <sub>T(AV)</sub>	T <sub>hs</sub>	55	°C			
1		2000	A			
I <sub>T(RMS)</sub>	T <sub>hs</sub>	25	°C			
1	50 Hz	17 800	Δ.			
I <sub>TSM</sub>	60 Hz	18 700	Α			
l <sup>2</sup> t	50 Hz	1591	kA <sup>2</sup> s			
141	60 Hz	1452	KA-S			
V <sub>DRM</sub> /V <sub>RRM</sub>		800 to 2000	V			
t <sub>q</sub>	Typical	150	μs			
TJ		-40 to 125	°C			

VOLTAGE RATINGS								
TYPE VOLTAGE CODE		V <sub>DRM</sub> /V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	$I_{DRM}/I_{RRM}$ MAXIMUM AT $T_J = T_J$ MAXIMUM $MA$				
	08	800	900					
VS-ST730CL	12	1200	1300					
	14	1400	1500	90				
	16	1600	1700	80				
	18	1800	1900					
	20	2000	2100					



ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL		VALUES	UNITS		
Maximum average on-state current	<b>I</b>	180° condu	ction, half sine v	wave	990 (375)	Α
at heatsink temperature	I <sub>T(AV)</sub>	double side	(single side) co	oled	55 (85)	°C
Maximum RMS on-state current	I <sub>T(RMS)</sub>	DC at 25 °C	heatsink tempe	erature double side cooled	2000	
		t = 10 ms	No voltage		17 800	
Maximum peak, one-cycle	ı	t = 8.3 ms	reapplied		18 700	A
non-repetitive surge current	I <sub>TSM</sub>	t = 10 ms	100 % V <sub>RRM</sub>		15 000	
		t = 8.3 ms	reapplied	Sinusoidal half wave,	15 700	
Mariana 121 for forture		t = 10 ms No voltage	initial $T_J = T_J$ maximum	1591		
	l <sup>2</sup> t	t = 8.3 ms	reapplied		1452	kA <sup>2</sup> s
Maximum I <sup>2</sup> t for fusing		t = 10 ms	100 % V <sub>RRM</sub>		1125	
		t = 8.3 ms	reapplied		1027	
Maximum I <sup>2</sup> √t for fusing	I <sup>2</sup> √t	t = 0.1 to 10	ms, no voltage	e reapplied	15 910	kA²√s
Low level value of threshold voltage	V <sub>T(TO)1</sub>	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	$I_{T(AV)}$ ), $T_J = T_J$ maximum	0.98	V
High level value of threshold voltage	V <sub>T(TO)2</sub>	$(I > \pi \times I_{T(AV)})$	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			\ \
Low level value of on-state slope resistance	r <sub>t1</sub>	(16.7 % x $\pi$ x $I_{T(AV)}$ < I < $\pi$ x $I_{T(AV)}$ ), $T_J = T_J$ maximum			0.32	mΩ
High level value of on-state slope resistance	r <sub>t2</sub>	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			0.27	1115.2
Maximum on-state voltage	$V_{TM}$	I <sub>pk</sub> = 2000 A, T <sub>J</sub> = T <sub>J</sub> maximum, t <sub>p</sub> = 10 ms sine pulse			1.62	V
Maximum holding current	Ι <sub>Η</sub>	T 05 °C anada ayanlı 10 V vaciatiya Is!			600	mA
Typical latching current	Iμ	T <sub>J</sub> = 25 °C, anode supply 12 V resistive load		1000	IIIA	

SWITCHING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 $\Omega$ , $t_r \le 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\le 80~\%~V_{DRM}$	1000	A/µs		
Typical delay time	t <sub>d</sub>	Gate current 1 A, $dl_g/dt = 1 A/\mu s$ $V_d = 0.67 \% V_{DRM}, T_J = 25 °C$	1.0			
Typical turn-off time	t <sub>q</sub>	$I_{TM}$ = 750 A, $T_J$ = $T_J$ maximum, $dI/dt$ = 60 A/ $\mu$ s, $V_R$ = 50 V, $dV/dt$ = 20 V/ $\mu$ s, gate 0 V 100 $\Omega$ , $t_p$ = 500 $\mu$ s	150	μs		

BLOCKING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum critical rate of rise of off-state voltage	dV/dt	T <sub>J</sub> = T <sub>J</sub> maximum linear to 80 % rated V <sub>DRM</sub>	500	V/µs		
Maximum peak reverse and off-state leakage current	I <sub>RRM</sub> , I <sub>DRM</sub>	$T_J = T_J$ maximum, rated $V_{DRM}/V_{RRM}$ applied	80	mA		



TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES		UNITS
FANAMETEN	STIMBOL		31 CONDITIONS	Тур.	Max.	ONITS
Maximum peak gate power	P <sub>GM</sub>	$T_J = T_J$ maximum,	$t_p \leq 5 \text{ ms}$	10	0.0	w
Maximum average gate power	P <sub>G(AV)</sub>	$T_J = T_J$ maximum,	f = 50  Hz, d% = 50	2	.0	VV
Maximum peak positive gate current	I <sub>GM</sub>	$T_J = T_J$ maximum,	$t_p \leq 5 \text{ ms}$	3	.0	Α
Maximum peak positive gate voltage	+ V <sub>GM</sub>	T - T maximum	+ < 5 ma	20		V
Maximum peak negative gate voltage	- V <sub>GM</sub>	$T_J = T_J$ maximum, $t_p \le 5$ ms			.0	] '
	I <sub>GT</sub>	T <sub>J</sub> = -40 °C	Maximum required gate trigger/ current/voltage are the lowest value which will trigger all units	200	-	
DC gate current required to trigger		T <sub>J</sub> = 25 °C		100	200	mA
		T <sub>J</sub> = 125 °C		50	-	
		T <sub>J</sub> = -40 °C		2.5	-	
DC gate voltage required to trigger	V <sub>GT</sub>	T <sub>J</sub> = 25 °C	12 V anode to cathode applied	1.8	3.0	V
		T <sub>J</sub> = 125 °C		1.1	-	
DC gate current not to trigger	I <sub>GD</sub>	T. T. was a vision was	Maximum gate current/voltage not to trigger is the maximum	1	0	mA
DC gate voltage not to trigger	$V_{GD}$	$T_J = T_J$ maximum	value which will not trigger any unit with rated V <sub>DRM</sub> anode to cathode applied	0.25		٧

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum operating junction temperature range	$T_{J}$		-40 to 125	°C	
Maximum storage temperature range	T <sub>Stg</sub>		-40 to 150		
Maximum thermal resistance, junction to heatsink	В	DC operation single side cooled	0.073		
Maximum thermal resistance, junction to heatsink	R <sub>thJ-hs</sub>	DC operation double side cooled	0.031	K/W	
Maximum thermal resistance, case to heatsink	R <sub>thC-hs</sub>	DC operation single side cooled	0.011	IV VV	
iviaximum thermal resistance, case to heatsink		DC operation double side cooled	0.006		
Mounting force, ± 10 %			14 700 (1500)	N (kg)	
Approximate weight			255	g	
Case style		See dimensions - link at the end of datasheet	B-PUK (TO-		

△R <sub>thJ-hs</sub> CONDUCTION							
CONDUCTION ANGLE	SINUSOIDAL	OIDAL CONDUCTION RECTANGULAR CONDUCTION			TEST CONDITIONS	LINUTO	
CONDUCTION ANGLE	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE	1EST CONDITIONS	UNITS	
180°	0.009	0.009	0.006	0.006	$T_J = T_J$ maximum		
120°	0.011	0.011	0.010	0.011			
90°	0.014	0.014	0.015	0.015		K/W	
60°	0.020	0.020	0.021	0.021			
30°	0.036	0.036	0.036	0.036			

#### Note

The table above shows the increment of thermal resistance RthJ-hs when devices operate at different conduction angles than DC



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## Vishay Semiconductors

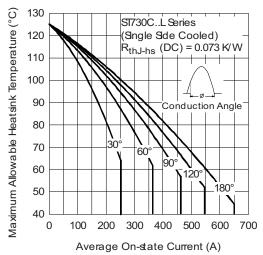


Fig. 1 - Current Ratings Characteristics

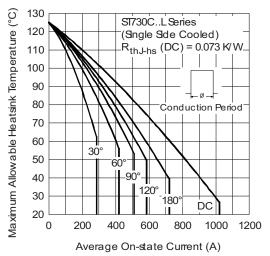


Fig. 2 - Current Ratings Characteristics

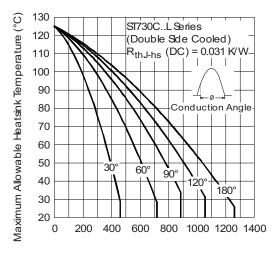


Fig. 3 - Current Ratings Characteristics

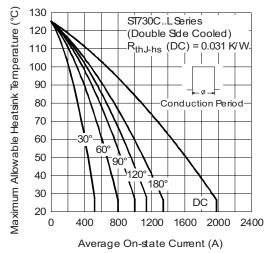


Fig. 4 - Current Ratings Characteristics

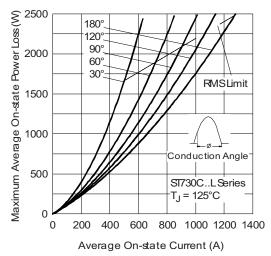


Fig. 5 - On-State Power Loss Characteristics

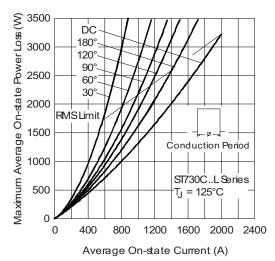
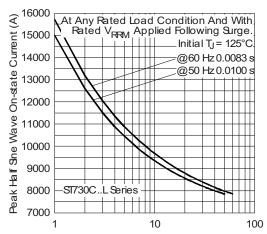


Fig. 6 - On-State Power Loss Characteristics



Number Of Equal Amplitude Half Cycle Current Pulses (N)

Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

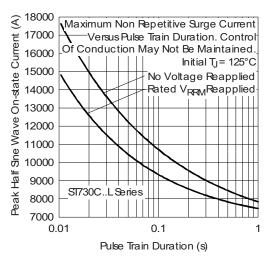


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

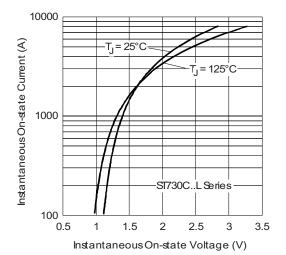


Fig. 9 - On-State Voltage Drop Characteristics

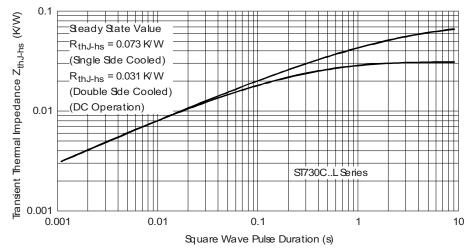


Fig. 10 - Thermal Impedance Z<sub>thJ-hs</sub> Characteristics

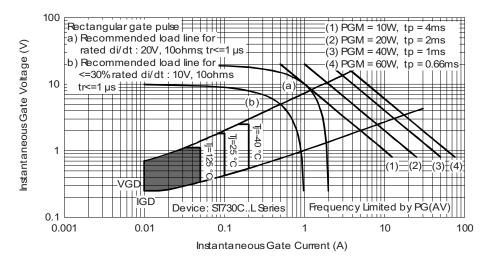
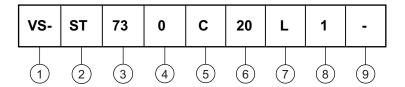


Fig. 11 - Gate Characteristics

#### **ORDERING INFORMATION TABLE**

**Device code** 



1 - Vishay Semiconductors product

2 - Thyristor

3 - Essential part number

4 - 0 = converter grade

5 - C = ceramic PUK

6 - Voltage code x 100 = V<sub>RRM</sub> (see Voltage Ratings table)

**7** - L = PUK case B-PUK (TO-200AC)

8 - 0 = eyelet terminals (gate and auxiliary cathode unsoldered leads)

1 = fast-on terminals (gate and auxiliary cathode unsoldered leads)

2 = eyelet terminals (gate and auxiliary cathode soldered leads)

3 = fast-on terminals (gate and auxiliary cathode soldered leads)

9 - Critical dV/dt: • None = 500 V/µs (standard selection)

• L = 1000 V/µs (special selection)

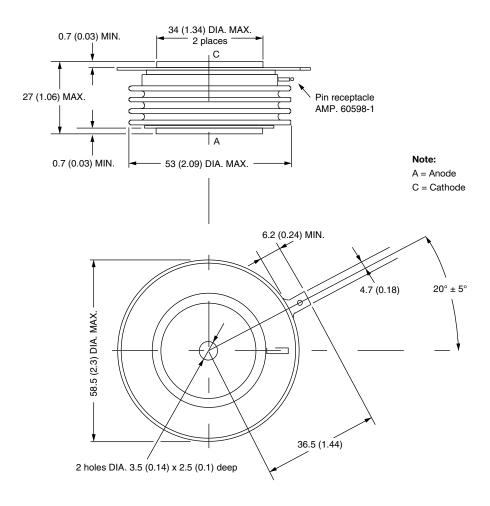
LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95076			



# **B-PUK (TO-200AC)**

#### **DIMENSIONS** in millimeters (inches)

Creepage distance: 36.33 (1.430) minimum Strike distance: 17.43 (0.686) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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